





80V NPN DARLINGTON TRANSISTOR IN SOT23

Features

- BVces > 80V
- **Epitaxial Planar Die Construction**
- Ideal for Low-Power Amplification and Switching
- **High-Current Gain**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

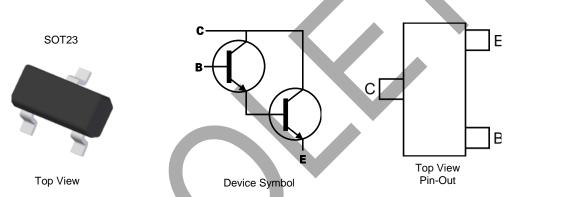
https://www.diodes.com/products/automotive/automotiveproducts/.

This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight 0.008 grams (Approximate)



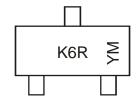
Ordering Information (Note 4)

Part Number	Pookogo	Package Marking Reel Size (inches) Tape Width (mm)		Packing		
Part Number Package		Marking Reel Size (inches)		rape widin (ililii)	Qty.	Carrier
MMBTA28-7-F	SOT23	K6R	7	8	3,000	Reel
MMBTA28-13-F	SOT23	K6R	13	8	10,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K6R = Product Type Marking Code YM = Date Code Marking

Y or \overline{Y} = Year (ex: K = 2023)

M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2008	-	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	V	-	K	L	М	N	Р	R	S	Т	U	V
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vcво	80	V
Collector-Emitter Voltage	Vces	80	V
Emitter-Base Voltage	VEBO	12	V
Continuous Collector Current	Ic	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	7	310	mW	
Power Dissipation	(Note 6)	PD	350		
Thermal Desigtance, lungtion to Ambient	(Note 5)	ב	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	357	C/W	
Thermal Resistance, Junction to Leads (Note 7)		Røjl	350	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

Notes:

- 5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 15mm x 15mm 1oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the leads).

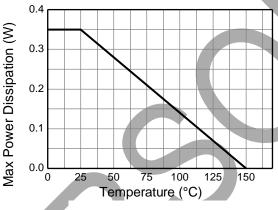


Figure 1. Derating Curve

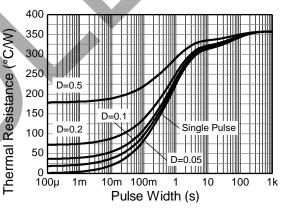
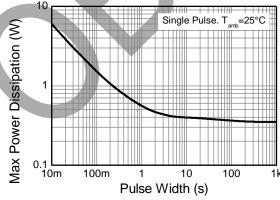


Figure 2. Transient Thermal Impedance



Pulse Power Dissipation

Figure 3. Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	ВУсво	80	_	_	V	Ic = 100µA, IE = 0
Collector-Emitter Breakdown Voltage (Note 8)	BVces	80	_	_	V	Ic = 100µA, V _{BE} = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	12	_	_	V	I _E = 100μA, I _C = 0
Collector Cut-off current	Ісво	_	_	100	nA	V _{CB} = 60V, I _E = 0
Collector Cut-on current	Ices	_	_	500	nA	Vce = 60V, VBE = 0
Emitter-Base Cut-off Current	I _{EBO}	_	_	100	nA	V _{EB} = 10V, I _C = 0
ON CHARACTERISTICS (Note 8)						
Static Forward Current Transfer Ratio	h _{FE}	10,000 10,000	_	_		Ic = 10mA, VcE = 5V Ic = 100mA, VcE = 5V
Collector-Emitter Saturation Voltage	VCE(sat)	_	_	1.2 1.5	V	$I_C = 10\text{mA}, I_B = 10\mu\text{A}$ $I_C = 100\text{mA}, I_B = 100\mu\text{A}$
Base-Emitter Turn-On Voltage	V _{BE(on)}	_		2.0	V	Ic = 100mA, VcE = 5V
SMALL SIGNAL CHARACTERISTICS (Note 8)						
Current Gain-Bandwidth Product	f⊤	125		_	MHz	I _C = 10mA, V _{CE} = 5V f = 100MHz
Output Capacitance	Cobo		8.0	_	pF	V _{CB} = 10V, f = 1MHz, I _E = 0
Input Capacitance	Cibo	-	15.0	<i>_</i>	pF	V _{EB} = 0.5V, f = 1MHz, I _C = 0

Note: 8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

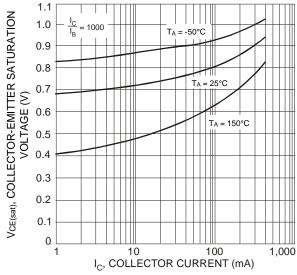


Figure 4. Typical Collector-Emitter Saturation Voltage vs. Collector Current

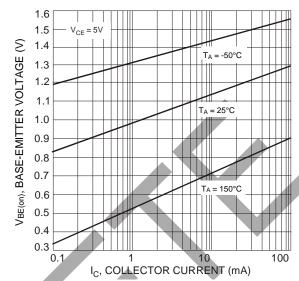


Figure 5. Typical Base-Emitter Voltage vs. Collector Current

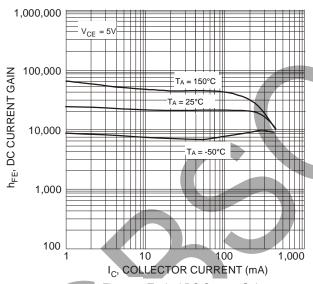


Figure 6. Typical DC Current Gain vs. Collector Current

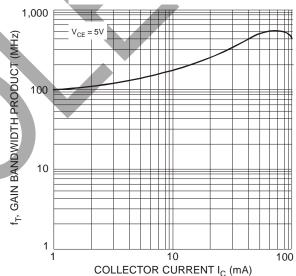


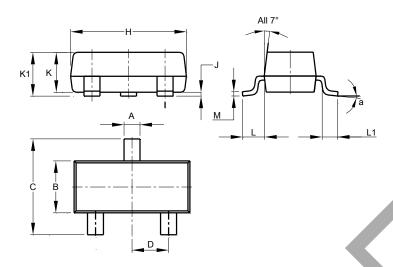
Figure 7. Typical Gain Bandwidth Product vs. Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

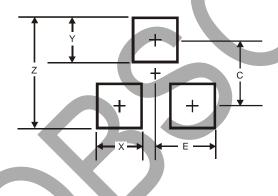


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
5	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
a	8° ¯						
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
Е	1.35



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